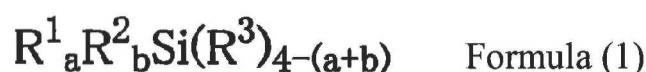


FILM-FORMING COMPOSITION CONTAINING SILICONE HAVING CROSSLINKING REACTIVITY

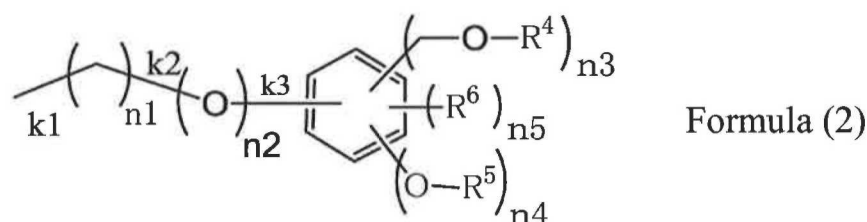
There is provided film-forming composition having favorable effects such as curability and embeddability and resist underlayer film for use in lithography process for semiconductor devices.

A film-forming composition comprising, as silane, hydrolyzable silane, hydrolysis product thereof, or hydrolysis-condensation product thereof, wherein

hydrolyzable silane includes hydrolyzable silane of Formula (1):



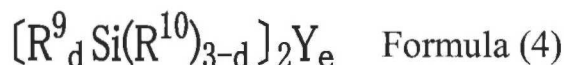
in Formula (1), R^1 is organic group of Formula (2) and is bonded to silicon atom through Si-C bond:



Film-forming composition, wherein the hydrolyzable silane is combination of hydrolyzable silane of Formula (1) with another hydrolyzable silane, wherein other hydrolyzable silane is at least one selected from group consisting of hydrolyzable silane of Formula (3):



and hydrolyzable silane of Formula (4):



Resist underlayer film, obtained by applying the resist underlayer film-forming composition on semiconductor substrate and baking.

Fig. 1